



**THE DATASHEET OF
DMC3032LSD-13**



Product Summary

Device	BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C (Notes 5 & 7)
Q1	30V	32mΩ @ V _{GS} = 10V	8.1A
		46mΩ @ V _{GS} = 4.5V	6.1A
Q2	-30V	39mΩ @ V _{GS} = -10V	-7A
		53mΩ @ V _{GS} = -4.5V	-5.6A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

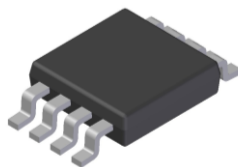
- Power Management Functions
- Analog Switch
- Load Switch

Features

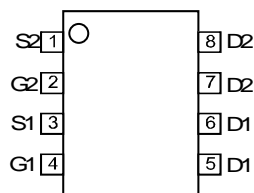
- Low On-Resistance
- N-Channel: 32mΩ @ 10V
46mΩ @ 4.5V
- P-Channel: 39mΩ @ -10V
53mΩ @ -4.5V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208^③
- Marking Information (See Page 2)
- Ordering Information
- Weight: 0.072 grams (Approximate)

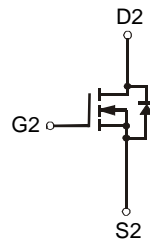


Top View

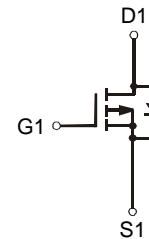


Top View

SO-8



N-Channel MOSFET

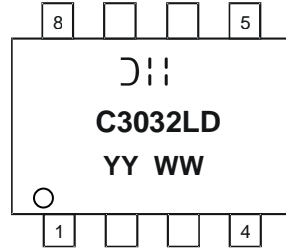


P-Channel MOSFET

Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3032LSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


D|| = Manufacturer's Marking
 C3032LD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 18 = 2018)
 WW = Week (01 to 53)

Maximum Ratings N-CHANNEL – Q1 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	I_D	8.1	A
		$T_A = +85^\circ\text{C}$		5.1	
Pulsed Drain Current (Note 6)			I_{DM}	25	A

Maximum Ratings P-CHANNEL – Q2 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	I_D	-7.0	A
		$T_A = +85^\circ\text{C}$		-4.5	
Pulsed Drain Current (Note 6)			I_{DM}	-25	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.45	2.1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	23	32	mΩ	V _{GS} = 10V, I _D = 7A
			32	46		V _{GS} = 4.5V, I _D = 5.6A
Forward Transfer Admittance	Y _{fs}	—	7.6	—	S	V _{DS} = 5V, I _D = 7A
Diode Forward Voltage (Note 7)	V _{SD}	—	0.7	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	404.5	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	51.8	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	45.1	—	pF	
Gate Resistance	R _g	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (10V)	Q _g	—	9.2	—	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 5.8A
Gate-Source Charge	Q _{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.8	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.4	—	ns	V _{GS} = 10V, V _{DS} = 15V, R _G = 3Ω, R _L = 2.6Ω
Turn-On Rise Time	t _r	—	6.18	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	13.92	—	ns	
Turn-Off Fall Time	t _f	—	2.84	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

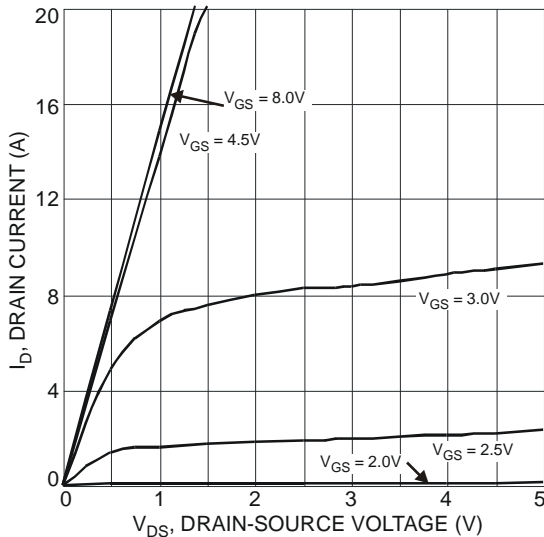


Fig. 1 Typical Output Characteristics

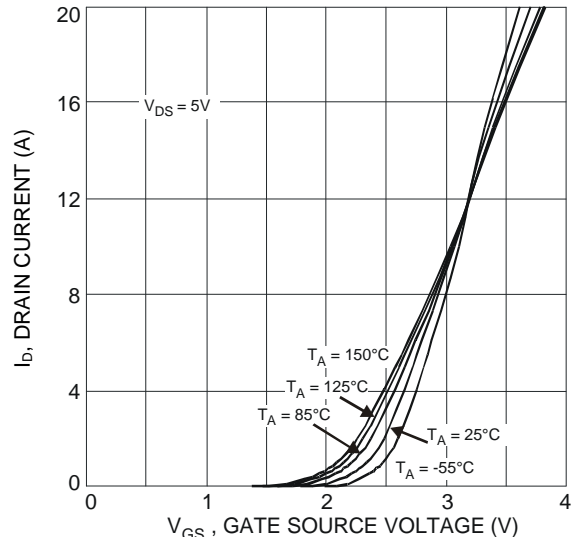


Fig. 2 Typical Transfer Characteristics

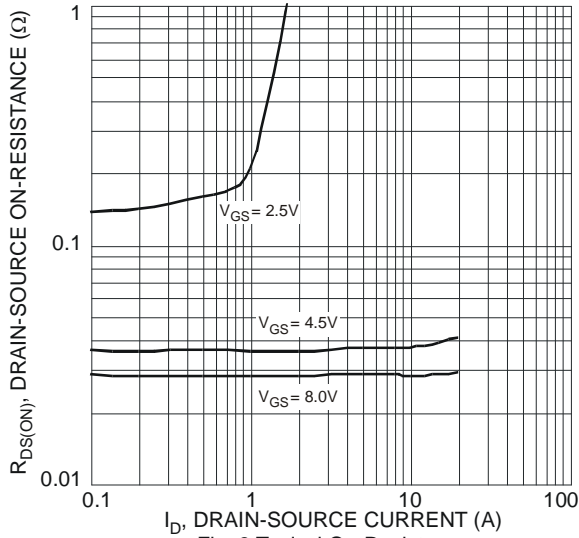


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

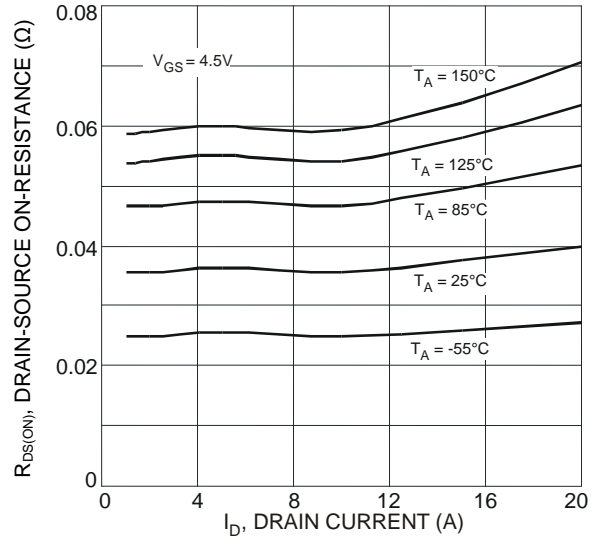


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

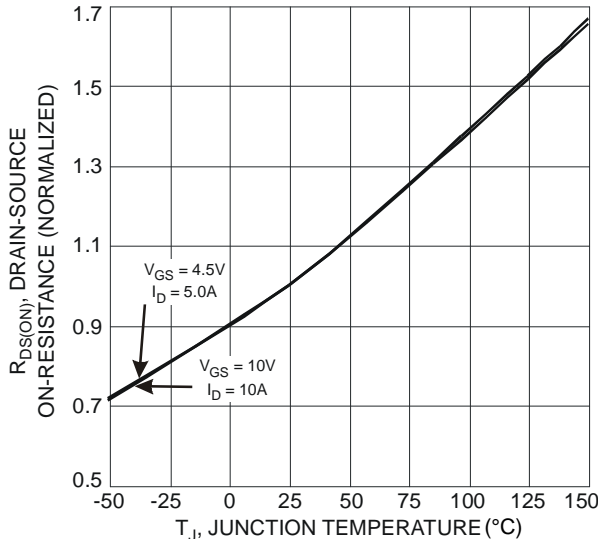


Fig. 5 On-Resistance Variation with Temperature

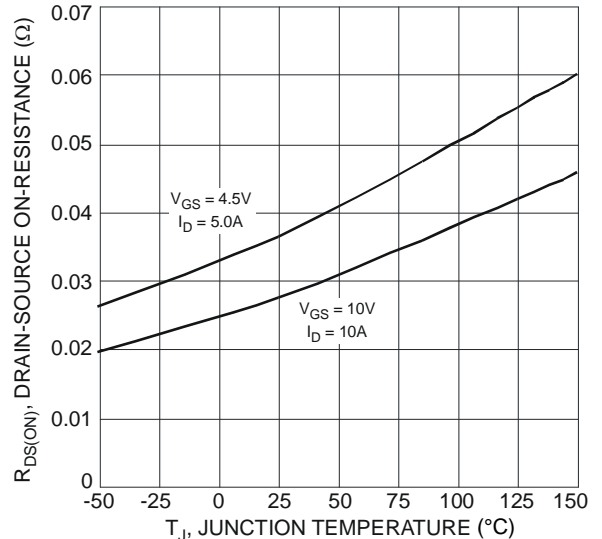


Fig. 6 On-Resistance Variation with Temperature

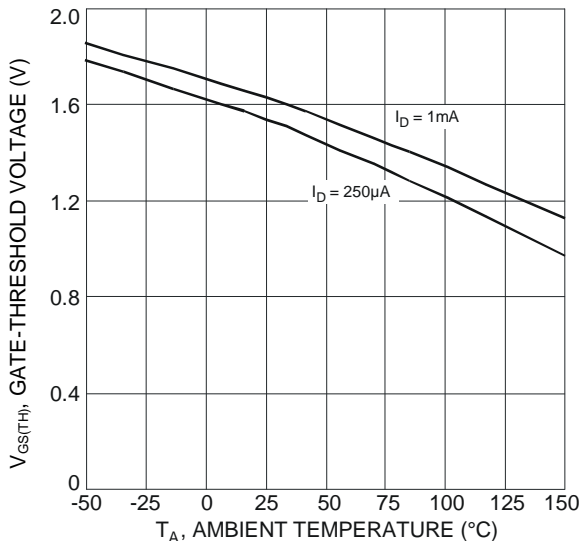


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

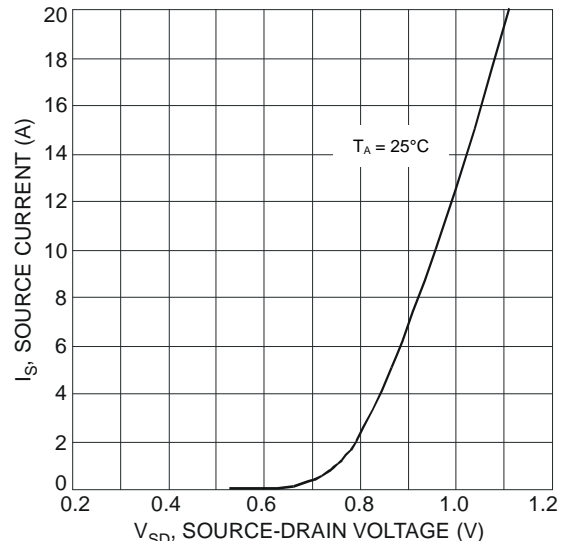
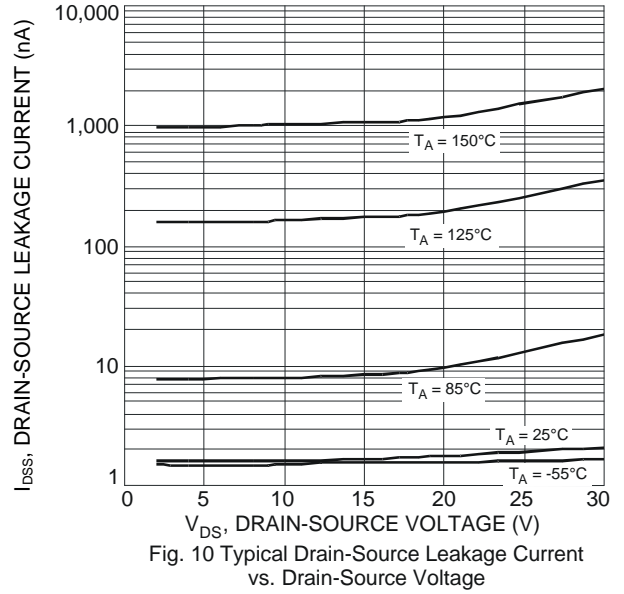
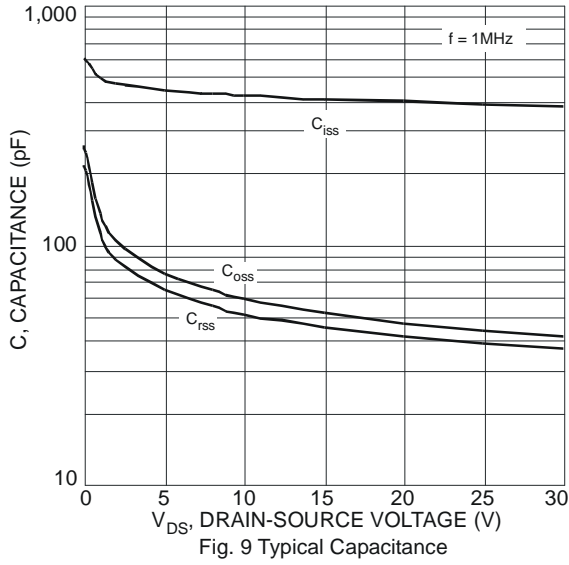


Fig. 8 Diode Forward Voltage vs. Current



Electrical Characteristics P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1	-1.7	-2.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	30	39	mΩ	V _{GS} = -10V, I _D = -4.3A V _{GS} = -4.5V, I _D = -3.7A
			42	53		
Forward Transfer Admittance	Y _{fs}	—	7	—	S	V _{DS} = -5V, I _D = -4.3A
Diode Forward Voltage (Note 7)	V _{SD}	—	-0.75	-1	V	V _{GS} = 0V, I _S = -1.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	1002	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oSS}	—	125	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	118	—	pF	
Gate Resistance	R _g	—	13	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (-4.5V)	Q _g	—	10.1	—	nC	V _{GS} = -4.5V/-10V, V _{DS} = -15V, I _D = -6A
Total Gate Charge (-10V)	Q _g	—	21.1	—	nC	
Gate-Source Charge	Q _{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	10.1	—	ns	V _{GS} = -10V, V _{DS} = -15V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _R	—	6.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	50.1	—	ns	
Turn-Off Fall Time	t _F	—	22.2	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

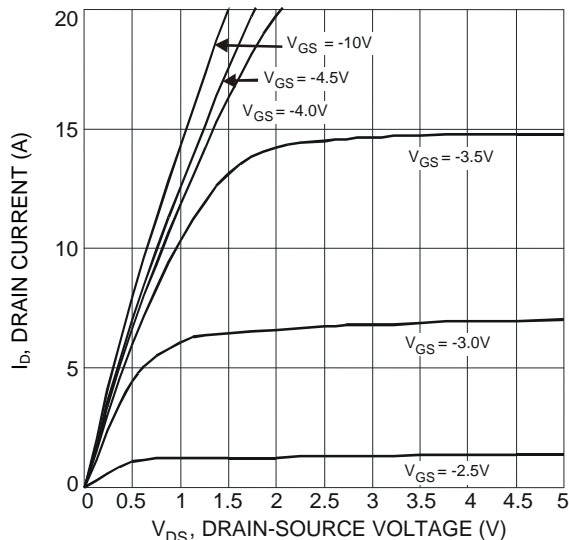


Fig. 11 Typical Output Characteristics

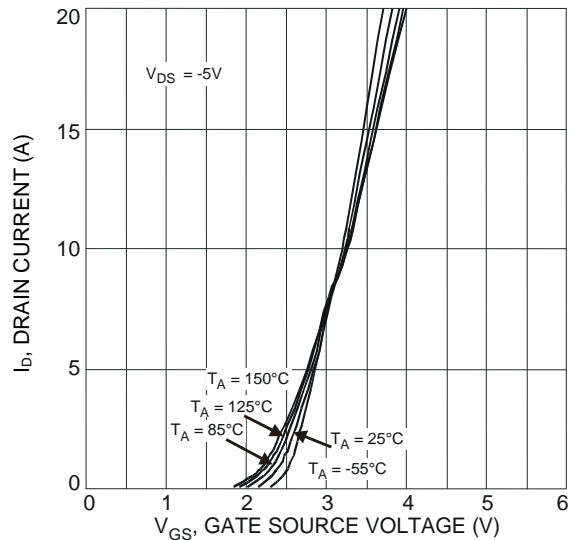


Fig. 12 Typical Transfer Characteristics

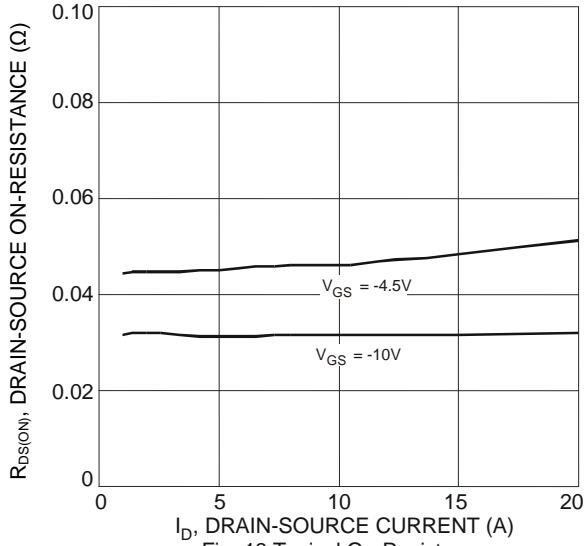


Fig. 13 Typical On-Resistance vs. Drain Current and Gate Voltage

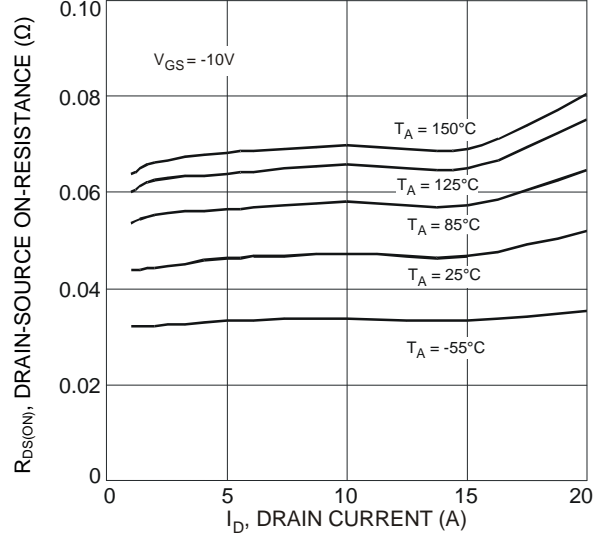


Fig. 14 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

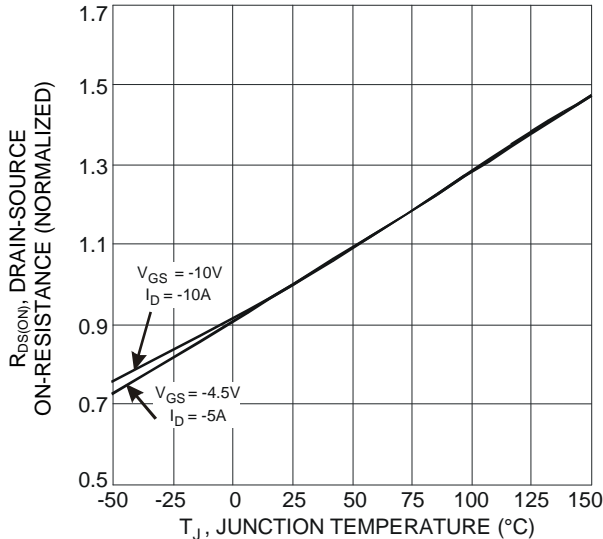


Fig. 15 On-Resistance Variation with Temperature

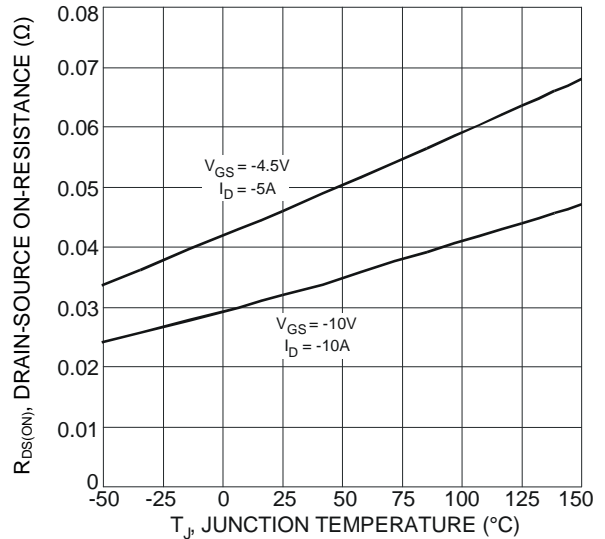


Fig. 16 On-Resistance Variation with Temperature

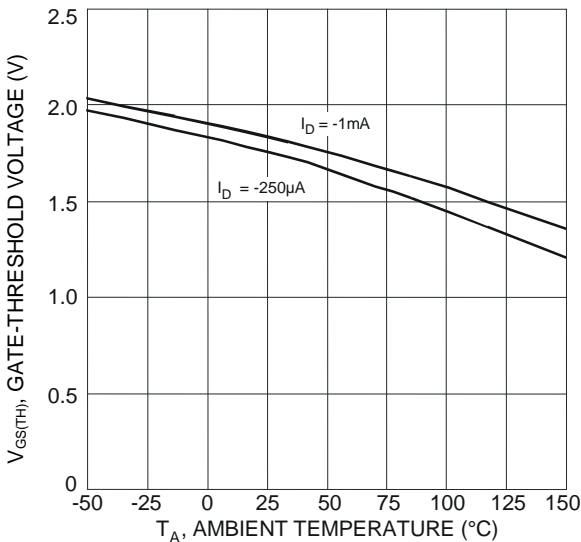


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

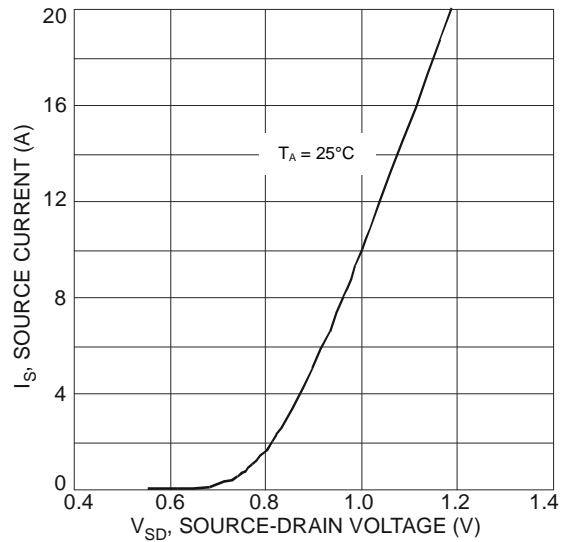
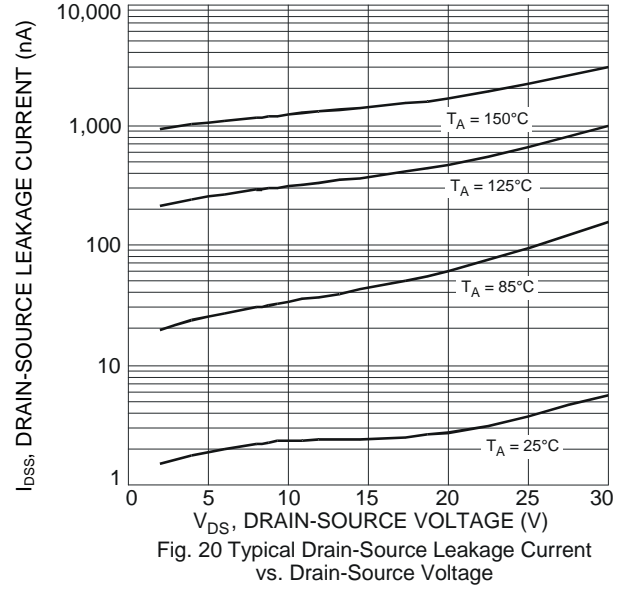
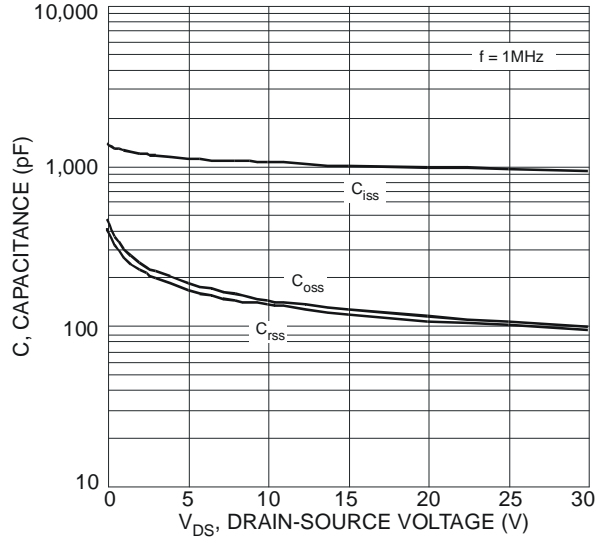


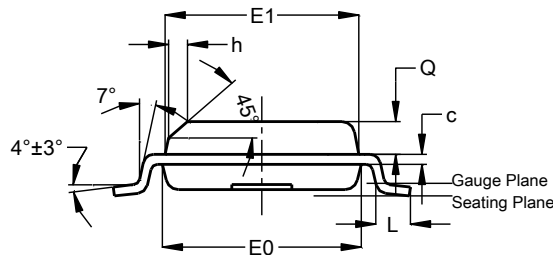
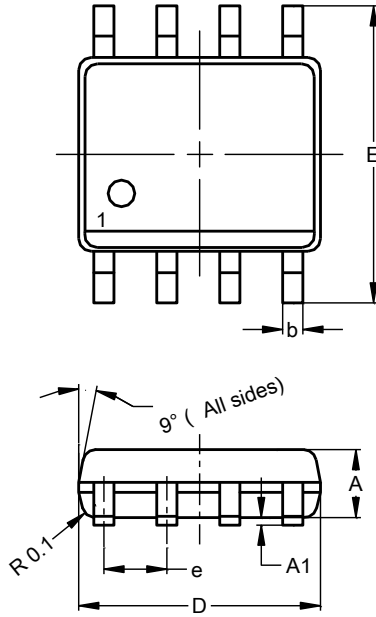
Fig. 18 Diode Forward Voltage vs. Current



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

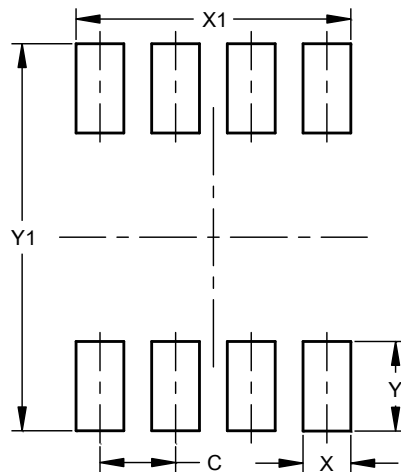


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

NEW PRODUCT

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